

ICFSI Program

Poster Session I

Chair: H. L. Alves

- P-MO-01** L. M. R. Scolfaro, S. F. Li, J. Schörmann, S. Potthast, S. C. P. Rodrigues, D. J. As, and K. Lischka. Structural and optical features of MBE grown cubic group-III nitride alloys .
- P-MO-02** B. N. Holland, G. Cabailh, N. Peltekis, C. McGuinness, A. A. Cafolla, G. Gavrilá, D. R. T. Zahn and I. T. McGovern. Orientation and ordering of the first monolayer of metal phthalocyanines on germanium (001)-2X1.
- P-MO-03** J. Bao and X. X. Liang. One and two mode behaviors of surface phonon-polaritons of ternary mixed crystal films.
- P-MO-04** D. Kropman, E. Mellikov, T. Kärner, I. Heinmaa, Ü. Ugaste, T. Laas, A. Medvid. Hydrogen interaction with point defects in the Si-SiO₂ system and its influence on the interface properties.
- P-MO-05** L. P. Bulat, I. A. Erofeeva, Y. V. Vorobiev and J. González-Hernández. Metal-semiconductor interface in extreme temperature conditions.
- P-MO-06** Y. V. Vorobiev, P. P. Horley, P. N. Gorley and J. González-Hernández. Calculation of electronic spectra of semiconductor nanostructures using the “mirror” boundary conditions.

- P-MO-07** Y. V. Vorobiev, P. P. Horley, P. N. Gorley and J. González-Hernández.
Calculation of electronic spectra of semiconductor nanostructures using the “mirror” boundary conditions.
- P-MO-08** V. P. Makhniy, V. V. Mel’nyk, M. M. Sletov, P. N. Gorley, P. P. Horley, Y. V. Vorobiev, and J. González-Hernández.
Optical properties of surface-modified ZnTe layers formed over ZnSe substrates
- P-MO-09** T. A. S. Pereira, S. R. Ferreira, A. S. Arruda, J. S. de Sousa, J. A. K. Freire and G. A. Farias.
Dielectric mismatch effects on tunneling currents through Si/SiO₂ and Si/HfO₂ quantum barrier.
- P-MO-10** S. C. P. Rodrigues, G. M. Sipahi, I. S. P. Marin, L. M. R. Scolfaro and E. F. da Silva Jr.
Study of additional confining potentials on the GeMn diluted ferromagnetic semiconductors.
- P-MO-11** R. Tetean, L. Chioncel, E. Burzo and I. G. Deac
The effect of lanthanide impurities on the physical properties of Heusler half-metallic ferromagnet Co₂MnSi.
- P-MO-12** Z. W. Yan and Genxiao Li.
Effect of electron-phonon interaction on the surface states in wurtzite nitride semiconductors.
- P-MO-13** Y. Huangfu and Z. W. Yan.
Quantum-confined Stark effect on shallow impurity state in nitride spherical quantum dot.

- P-MO-14** R. R. Andrade, D. R. Miquita, M. V. B. Moreira, J. C. González, R. Magalhães-Paniago, M. I. N. da Silva, and A. G. de Oliveira.
Growth conditions dependence of the structure of iron silicide thin films grown by reactive deposition epitaxy on Si(111).
- P-MO-15** S. Ossicini, M. Bruno, M. Palummo and R. Del Sole.
Excitonic effects on the optical properties of germanium and silicon nanowires.
- P-MO-16** P. Mutombo and V. Cháb.
The interaction of carbon with Si(111):As-(1x1) and Si(111):H-(1x1) surfaces.
- P-MO-17** M. Svec, P. Jelinek, C. Gonzales, P. Shukrynuau and V. Chab.
LDOS maps on Si(111)-7x7: STS facing the theory.
- P-MO-18** S. I. Drapak, A. P. Bakhtinov and Z. D. Kovalyuk.
Noise characteristics of thermally oxidated InSe single crystals.
- P-MO-19** S. I. Drapak, S. V. Gavrylyuk, Z. D. Kovalyuk, O. S. Lytvyn.
Aged-induced phase formation on cleft surface of layered GaSe single crystals.
- P-MO-20** P. Shukrynuau, M. Švec, M. Vondráček, Pingo Mutombo, V. Dudr, F. Šutara, V. Matolín, K. C. Prince and V. Cháb.
Photoemission and STM characterization of Ta/Si(111)-7x7 interface.

- P-MO-21** R. Palmieri, H. Boudinov, C. Radtke and E. F. da Silva Jr.
Effect of the Oxidation Process on SiO₂/4H-SiC Interface Electrical Characteristics.
- P-MO-22** R. H. Miwa, W. Orellana, and G. P. Srivastava.
Iron stripes patterned by Bi-nanolines on silicon surfaces.
- P-MO-23** M. Oshikiri, M. Boero, A. Matsushita, and J. Ye.
Water Molecule Adsorption Properties on the InVO₄ (001) Surface.
- P-MO-24** S. J. So, H.J. Kim, D. Cha and C. S. Han.
Photoluminescence of ZnO in Metal Exchanged Zeolite Y.
- P-MO-25** M. Maekawa and A. Kawasuso.
Characterization of SiC-on-insulator structure formed by ion implantation using positron annihilation spectroscopy.
- P-MO-26** G. Trummer, G. Hlawacek, D. Pressl and C. Teichert.
Growth of Phospholipid Membrane Systems on self-organized semiconductor templates.
- P-MO-27** R. Miotto, P. P. Fávero, and A. C. Ferraz.
A comparative study of the adsorption and dissociation of vinylacetic acid and acrylic acid on Silicon (001).
- P-MO-28** C. S. A. Lima, P. M. A. Farias, B. S. Santos, A. Fontes, R. C. B. Q. Figueiredo, C. R. Chaves, A. Galembeck, A. A. S. Vieira, A. G. Castro-Neto, D. C. N. da Silva, F. D. Menezes and R. Ferreira.
Quantum dots bioconjugates: Anti-cancer activity.

- P-MO-29** W. Zhu and A. Freundlich.
Unusually high Be diffusivity in nitrogen doped GaAs.
- P-MO-30** Z. J. Horváth.
Evaluation of Schottky junction parameters from current-voltage characteristics exhibiting large excess currents.
- P-MO-31** F. D. de Menezes, A. G. Brasil Jr, C. N. Jovino, E. L. Mariano, B. S. Santos, P. M. A. Farias, A. Fontes and R. Ferreira.
Semiconductor nanocrystals obtained by colloidal chemistry for biological applications.
- P-MO-32** P. Deák, T. Frauenheim, T. Hornos, and A. Gali.
Theoretical study of the effect of nitridation on the interface states of the SiC/SiO₂ system.
- P-MO-33** V. G. A. Carneiro, J. C. da Costa and J.G. Guimarães.
Considerations about interconnection limits on basic subcircuits with single-electron tunneling devices.
- P-MO-34** A. Kawaharazuka, I. Yoshida and Y. Horikoshi.
Area selective epitaxy of GaAs by migration-enhanced epitaxy with As₂ and As₄ arsenic sources.
- P-MO-35** I. Ulfat, J. Adell, J. Sadowski, L. Ilver, and J. Kanski.
Electron spectroscopic studies of nanowires formed by (GaMn)As growth on GaAs.
- P-MO-36** E. Ahn, K. Park, B. Kim, Y. D. Kim, and E. Yoon.
Real-time monitoring of InAs QD growth procedure on InP substrate by Spectral Reflectance.

- P-MO-37** T. J. Kim¹, J. J. Yoon, Y. D. Kim, D. E. Aspnes, M. V. Klein, D-S. Ko, Y-W. Kim, V. Elarde, and J. Coleman.
Analysis on the Interface layer by spectroscopic ellipsometry.
- P-MO-38** T. H. Ghong, Y. D. Kim, E. Ahn, E. Yoon, S. J. Ahn, and G. C. Yi.
Application of spectral reflectance for monitoring ZnO nanorod growth.
- P-MO-39** M. L. Gómez-Herrera, J. L. Herrera-Pérez, P. Rodríguez-Fregoso, and J. G. Mendoza-Alvarez.
Low temperature photoluminescence characterization of Zn-doped $\text{In}_x\text{Ga}_{1-x}\text{As}_y\text{Sb}_{1-y}$ epitaxial layers for photovoltaic applications.
- P-MO-40** M. N. d' Eurydice, G. M. Sipahi, S. C. P. Rodrigues, E. F. da Silva Jr., L. M. R. Scolfaro.
Optical and electronic properties calculations for GaN and AlN diluted magnetic heterostructures.
- P-MO-41** E. A. Morais, and L. V. A. Scalvi.
Electron Trapping and Optical properties of intergrain interface in SnO₂ doped with rare-earth trivalent ions.
- P-MO-42** G. S. Belo, B. J. P. da Silva, E. A. de Vasconcelos and E. F. da Silva Jr.
Optical and Electrical Properties of ITO Thin Films Synthesized by Reactive Thermal Evaporation